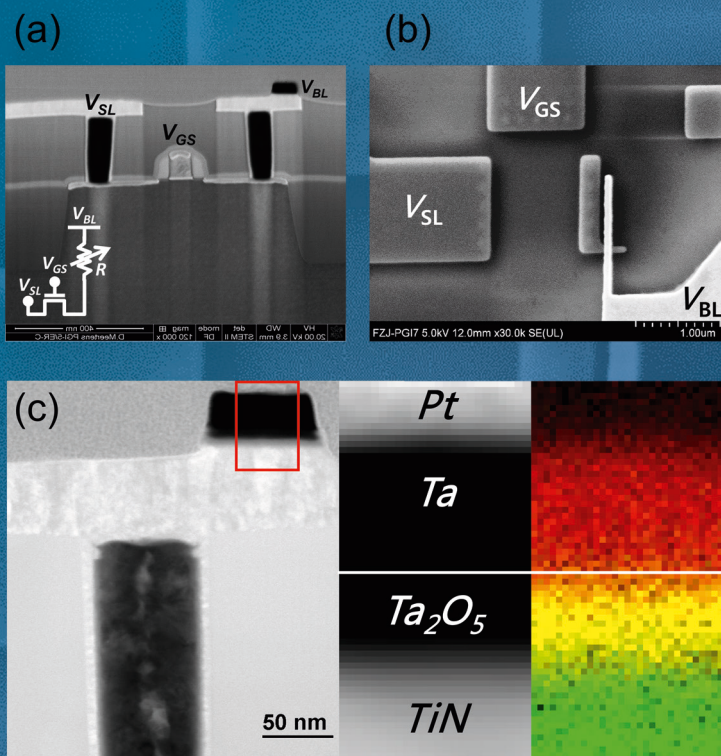


Investigation of switching mechanism in Ta_2O_5 -based ReRAM devices

Wonjoo Kim



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